



STC128M

NPN Silicon Transistor

Features

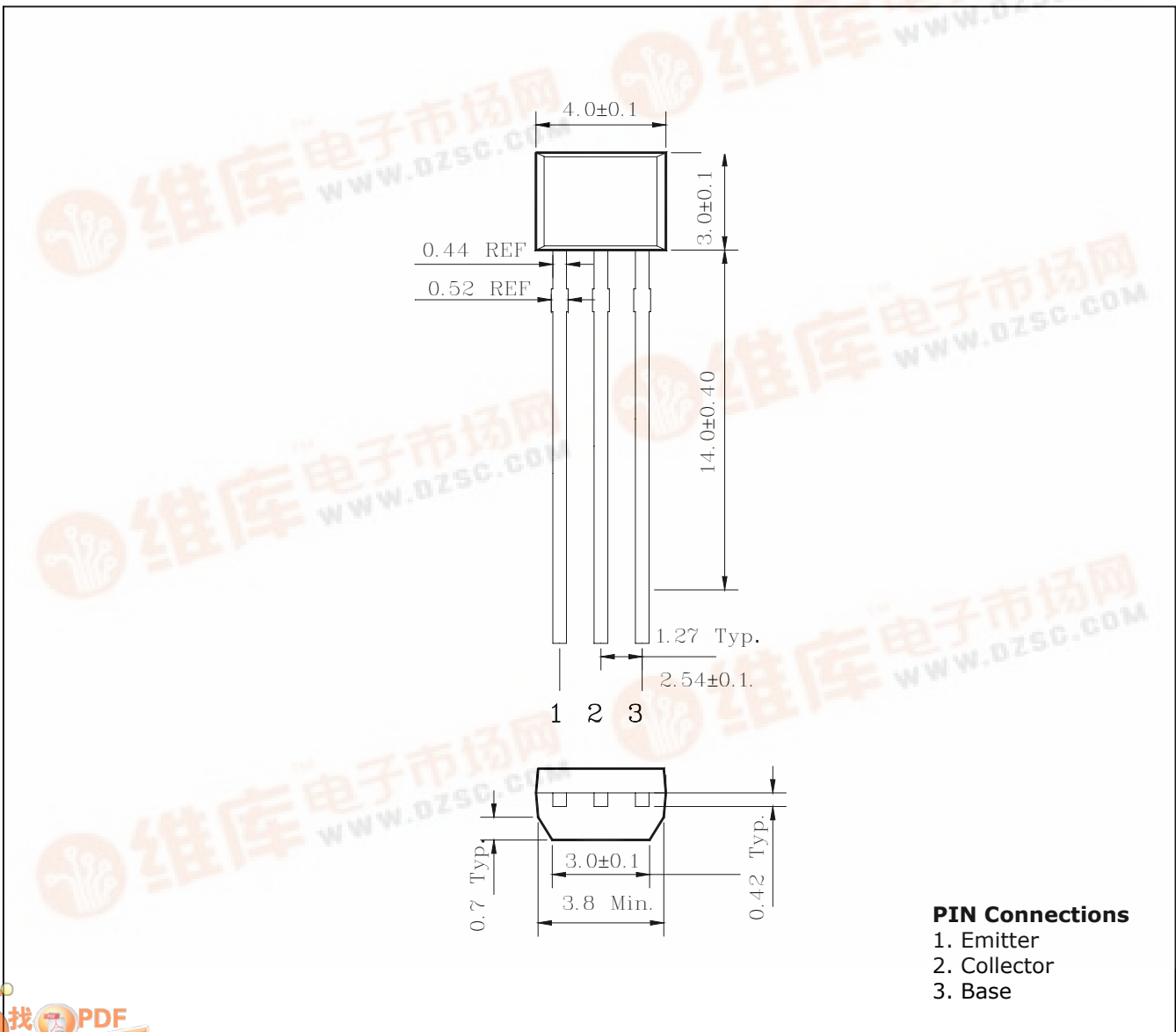
- Low saturation medium current application
- Extremely low collector saturation voltage
- Suitable for low voltage large current drivers
- High DC current gain and large current capability
- Low on resistance : $R_{ON}=0.6\Omega(\text{Max.})$ ($I_B=1\text{mA}$)

Ordering Information

Type NO.	Marking	Package Code
STC128M	C128	TO-92M

Outline Dimensions

unit : mm



Absolute maximum ratings

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	20	V
Collector-Emitter voltage	V_{CEO}	15	V
Emitter-base voltage	V_{EBO}	6.5	V
Collector current	I_C	1	A
Collector dissipation	P_C	400	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~150	°C

Electrical Characteristics

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C=50\mu A, I_E=0$	20	-	-	V
Collector-Emitter breakdown voltage	BV_{CEO}	$I_C=1mA, I_B=0$	15	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	$I_E=50\mu A, I_C=0$	6.5	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$	-	-	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6V, I_C=0$	-	-	0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	150	-	-	-
Collector-Emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	-	0.1	0.3	V
Transistor frequency	f_T	$V_{CE}=5V, I_C=50mA$	-	260	-	MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	5	-	pF
On resistance	R_{ON}	$f=1KHz, I_B=1Ma, V_{IN}=0.3V$	-	0.6	-	Ω

Electrical Characteristic Curves

Fig. 1 $P_C - T_a$

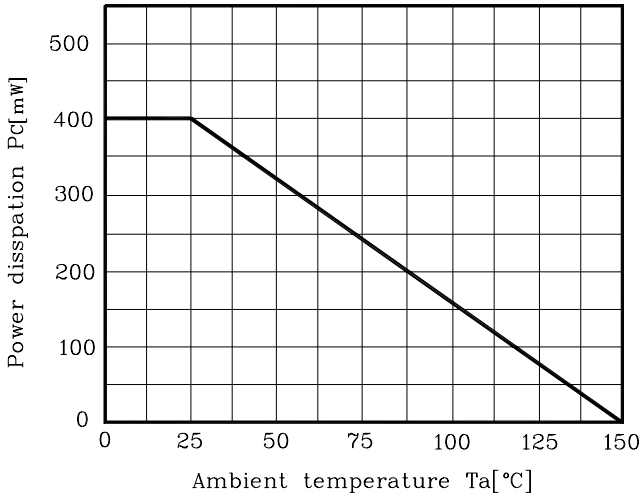


Fig. 1 $C_{ob} - V_{CB}$

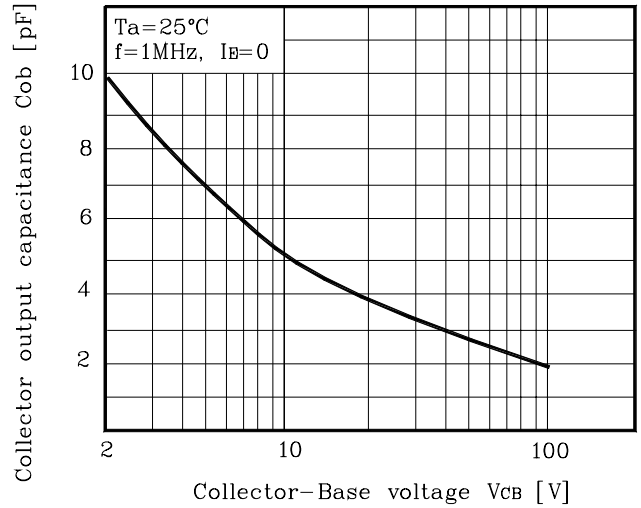


Fig. 3 $h_{FE} - I_C$

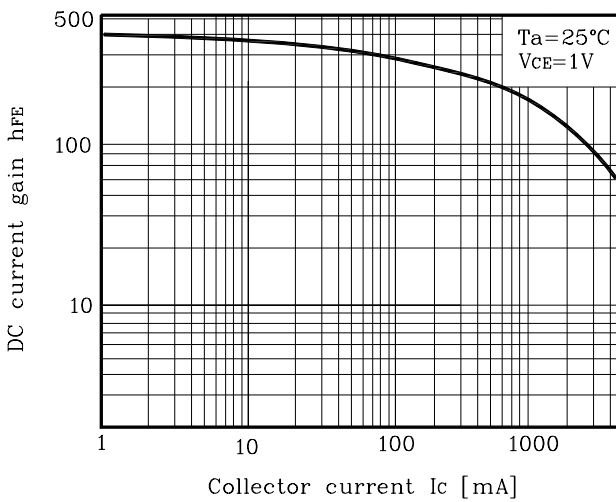


Fig. 1 $V_{CE(sat)} - I_C$

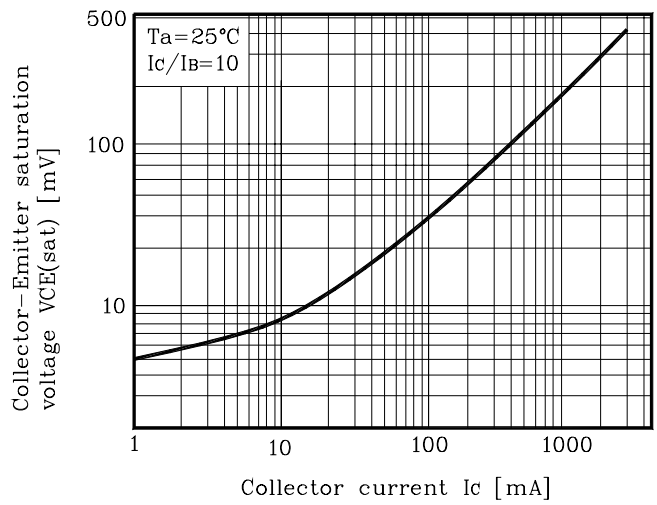


Fig. 4 $R_{ON} - I_B$

